

Patent Abstracts of Japan

PUBLICATION NUMBER : 08208380  
PUBLICATION DATE : 13-08-96

APPLICATION DATE : 25-01-95  
APPLICATION NUMBER : 07010068

APPLICANT : NIPPON STEEL CORP;

INVENTOR : KANETANI MASATOSHI;

INT.CL. : C30B 23/00 C30B 29/36 // H01L 33/00

TITLE : PRODUCTION OF SINGLE-CRYSTALLINE SILICON CARBIDE

ABSTRACT : PURPOSE: To grow high-quality single-crystalline silicon carbide almost free from defects.

CONSTITUTION: When a silicon carbide single crystal is grown by a sublimation-recrystallization method using a seed crystal, 1ppm to 90% gaseous hydrogen is incorporated into inert gas such as Ar and the resultant gas is used as atmospheric gas.

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